

## ABSTRACT

The invention provides Group III nitride semiconductor crystals of a size appropriate for semiconductor devices and methods for manufacturing the same, Group III nitride semiconductor devices and methods for manufacturing the same, and light-emitting appliances. A method of manufacturing a Group III nitride semiconductor crystal includes a process of growing at least one Group III nitride semiconductor crystal substrate on a starting substrate, a process of growing at least one Group III nitride semiconductor crystal layer on the Group III nitride semiconductor crystal substrate, and a process of separating a Group III nitride semiconductor crystal, constituted by the Group III nitride semiconductor crystal substrate and the Group III nitride semiconductor crystal layer, from the starting substrate, and is characterized in that the Group III nitride semiconductor crystal is 10  $\mu\text{m}$  or more but 600  $\mu\text{m}$  or less in thickness, and is 0.2 mm or more but 50 mm or less in width.